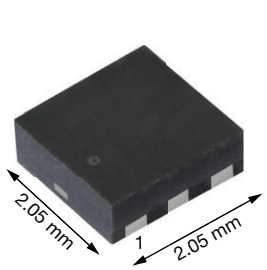
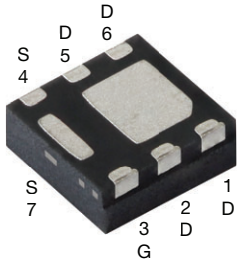
Automotive N-Channel 80 V (D-S) 175 °C MOSFET

PowerPAK® SC-70W-6L Single



Top View



Bottom View

Marking Code: Q4XXXX

FEATURES

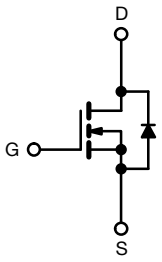
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- Wettable flank terminals
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

Pb-free

RoHS COMPLIANT

HALOGEN FREE



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	80
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0800
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0950
I_D (A)	5.63
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK SC-70W-6L
Lead (Pb)-free and halogen-free	SQA604CEJW (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	80	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	T_C = 25 °C [a]	I_D	5.63	A
	T_C = 125 °C		5.13	
Continuous source current (diode conduction) [a]		I_S	5.63	
Pulsed drain current [a]		I_{DM}	21	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	9	
Single pulse avalanche energy		E_{AS}	4.05	mJ
Maximum power dissipation	T_C = 25 °C	P_D	13.6	W
	T_C = 125 °C		4.5	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [d, e]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [c]	R_{thJA}	90	°C/W
Junction-to-case (drain)		R_{thJC}	11	

Notes

a. Package limited
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
c. When mounted on 1" square PCB (FR4 material)
d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin.
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

For technical questions, contact: automos.techsupport@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		80	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		1.5	2	2.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 80 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 80 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 80 V, T_J = 175 °C	-	-	150	
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	5	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 3 A	-	0.0593	0.0800	Ω
		V_{GS} = 10 V	I_D = 3 A, T_J = 125 °C	-	-	0.1405	
		V_{GS} = 10 V	I_D = 3 A, T_J = 175 °C	-	-	0.1724	
		V_{GS} = 4.5 V	I_D = 2.5 A	-	0.0690	0.0950	
Forward transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 3 A		-	10.2	-	S
Dynamic [b]							
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	315	445	pF
Output capacitance	C_{oss}			-	63	90	
Reverse transfer capacitance	C_{rss}			-	9	13	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 40 V, I_D = 5 A	-	6.5	9.8	nC
Gate-source charge [c]	Q_{gs}			-	1.3	-	
Gate-drain charge [c]	Q_{gd}			-	1.2	-	
Gate resistance	R_g	f = 1 MHz		0.62	1.24	1.86	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 40 V, R_L = 40 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_g = 1 Ω		-	5	10	ns
Rise time[c]	t_r			-	3	6	
Turn-off delay time [c]	$t_{d(off)}$			-	14	22	
Fall time [c]	t_f			-	5	10	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed current [a]	I_{SM}			-	-	21	A
Forward voltage	V_{SD}	I_F = 3 A, V_{GS} = 0 V		-	0.85	1.2	V
Body diode reverse recovery time	t_{rr}	I_F = 1 A, di/dt = 100 A/µs		-	17	34	ns
Body diode reverse recovery charge	Q_{rr}			-	10.2	20.5	nC
Reverse recovery fall time	t_a			-	12	-	ns
Reverse recovery rise time	t_b			-	5	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-1.03	-	A

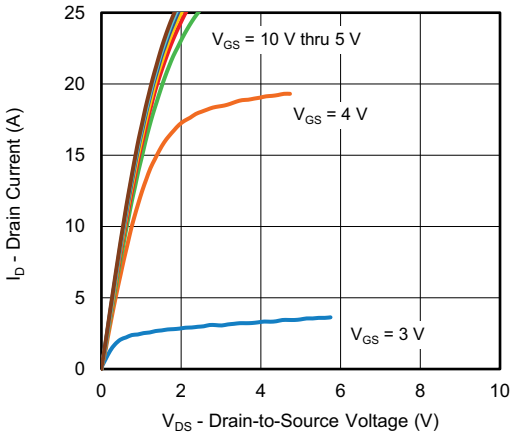
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

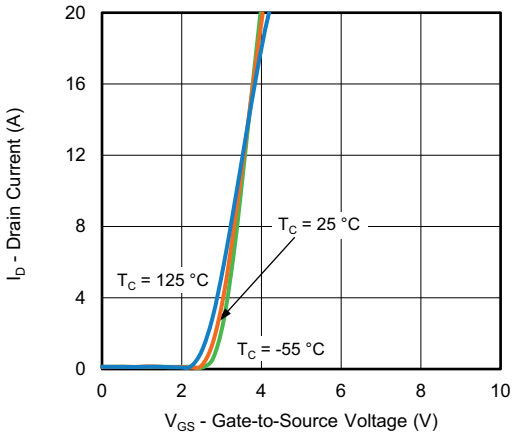
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

For technical questions, contact: automos.techsupport@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

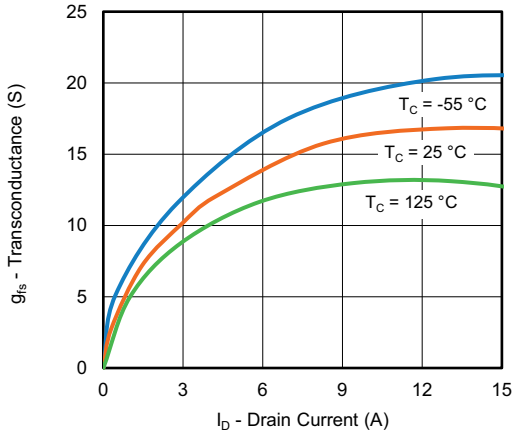
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



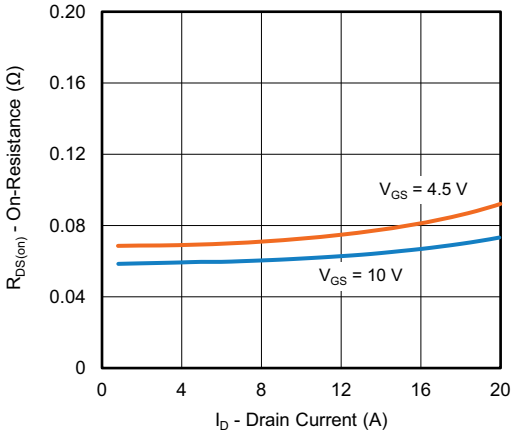
Output Characteristics



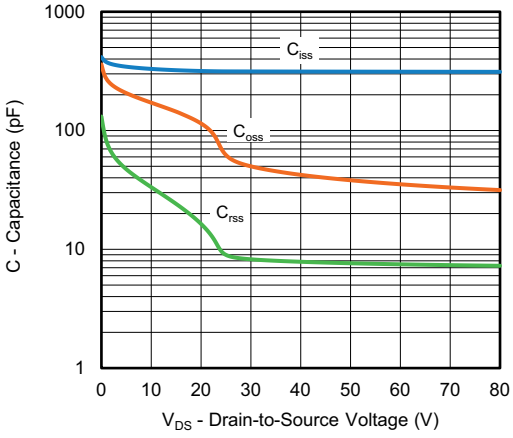
Transfer Characteristics



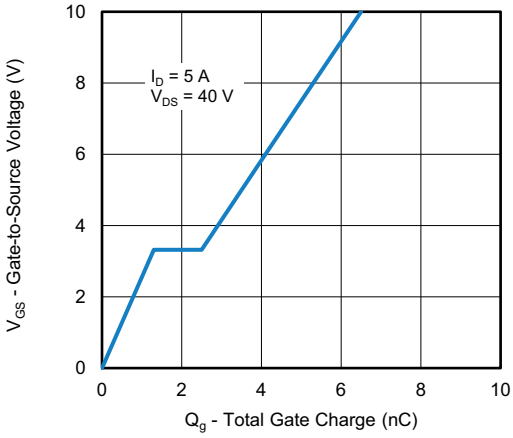
Transconductance



On-Resistance vs. Drain Current



Capacitance

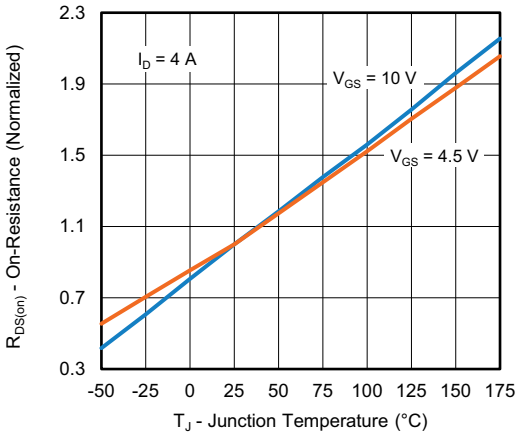


Gate Charge

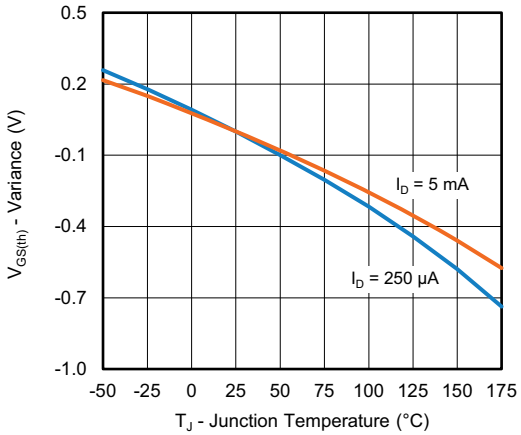
For technical questions, contact: automos.techsupport@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

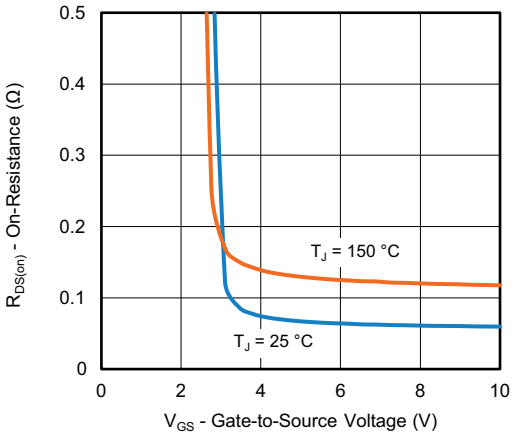
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



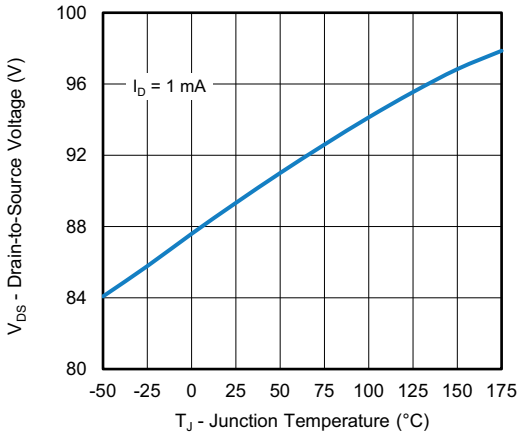
On-Resistance vs. Junction Temperature



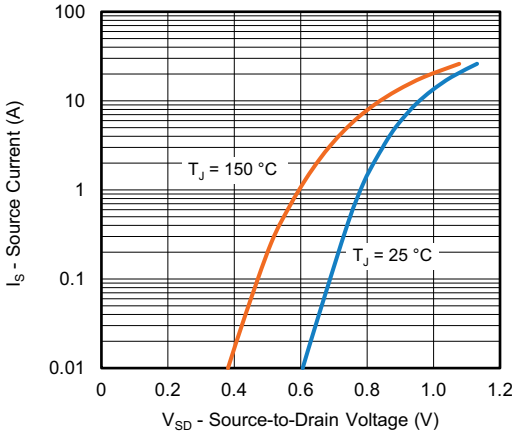
Threshold Voltage



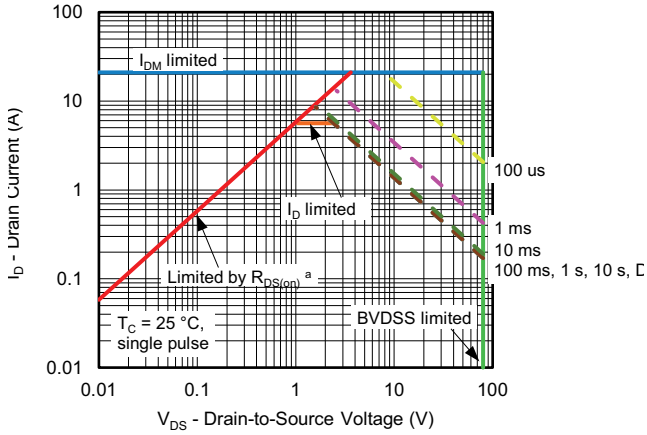
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



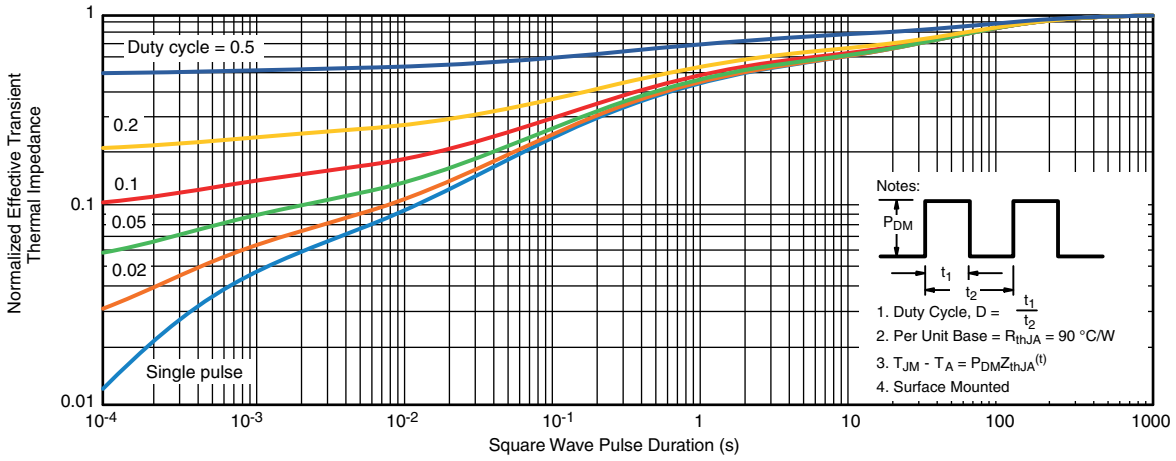
Safe Operating Area

Note

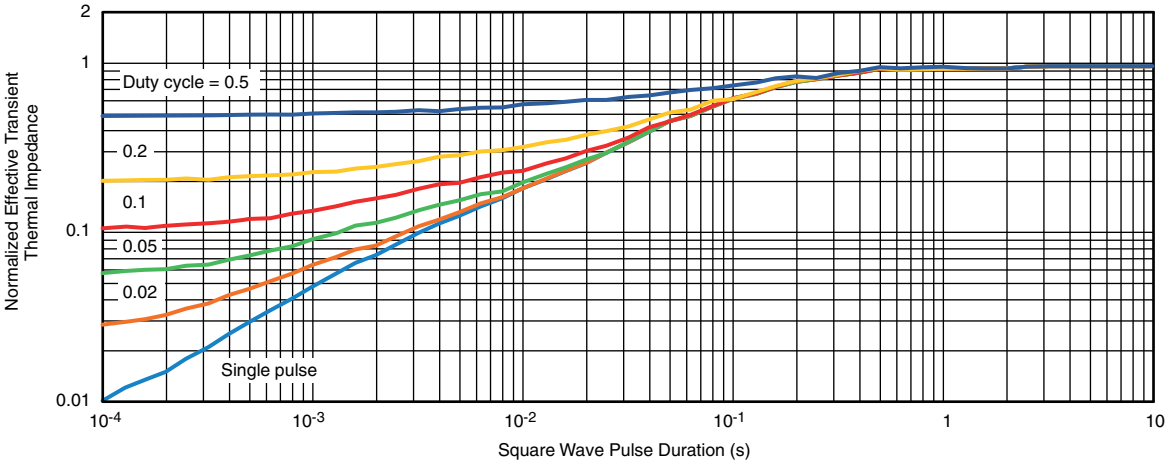
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

For technical questions, contact: automos.techsupport@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



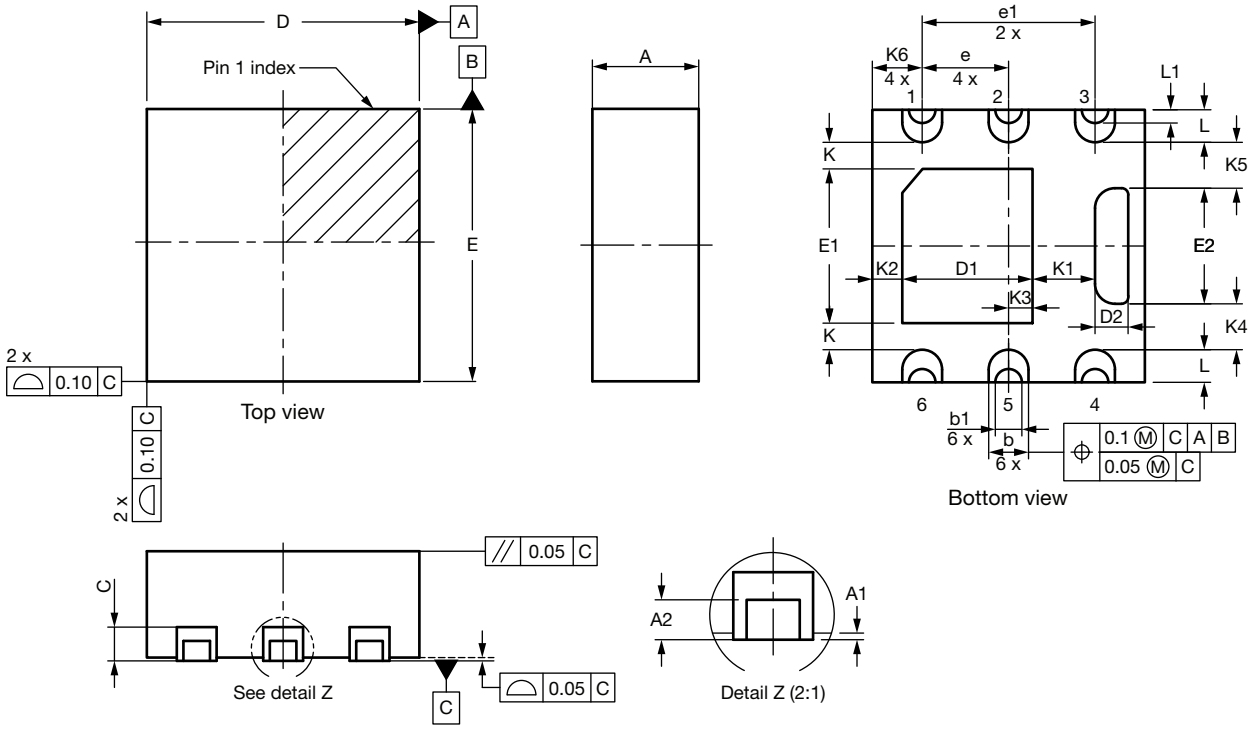
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62007.

For technical questions, contact: automos.techsupport@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

PowerPAK® SC70W-6L SIDEWETTABLE



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.02	0.05	0.000	0.001	0.002
A2	0.10	-	-	0.004	-	-
b	0.25	0.30	0.35	0.010	0.012	0.014
b1	0.15	0.20	0.23	0.006	0.008	0.009
C	0.20	0.25	0.30	0.008	0.010	0.012
D	1.95	2.05	2.15	0.077	0.081	0.085
D1	0.88	0.98	1.08	0.035	0.039	0.043
D2	0.20	0.25	0.30	0.008	0.010	0.012
E	1.95	2.05	2.15	0.077	0.081	0.085
E1	1.06	1.16	1.26	0.042	0.046	0.050
E2	0.82	0.87	0.92	0.032	0.034	0.036
e	0.65 BSC			0.026 BSC		
e1	1.30 BSC			0.051 BSC		
K	0.20 typ.			0.008 typ.		
K1	0.47 typ.			0.019 typ.		
K2	0.23 typ.			0.009 typ.		
K3	0.18 typ.			0.007 typ.		
K4	0.35 typ.			0.014 typ.		
K5	0.35 typ.			0.014 typ.		
K6	0.38 typ.			0.015 typ.		
L	0.15	0.25	0.35	0.006	0.010	0.014
L1	-	0.10	-	-	0.004	-
ECN: C19-1644-Rev. A, 10-Jan-2020 DWG: 6076						

Notes

- Package outline exclusive of mold flash and metal burr
- Package outline inclusive of plating

For technical questions, contact: pmostechsupport@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2024 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED